

<b>Notice of References Cited</b>	Application/Control No. 09/358,388	Applicant(s)/Patent Under Reexamination UMEZAWA ET AL.	
	Examiner Anh D. Mai	Art Unit 2814	Page 1 of 1

**U.S. PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-			
	B	US-			
	C	US-			
	D	US-			
	E	US-			
	F	US-			
	G	US-			
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	J	US-			
	K	US-			
	L	US-			
	M	US-			

**FOREIGN PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N	RD-327019				
	O					
	P					
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	S					
	T					

**NON-PATENT DOCUMENTS**

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Anonymous, RD-327019 Semiconductor for Trench Isolation - Produced by Depositing TetraEthylOthoSilicate Film by CVD., Derwent. July 10, 1991.
	V	
	W	
	X	

\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
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